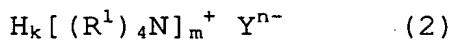
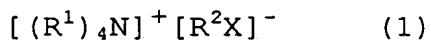


ABSTRACT OF THE DISCLOSURE

Provided are a composition for forming film which can form porous film excelling in dielectric constant, adhesiveness, uniformity of the film, mechanical strength and having low hygroscopicity; porous film and a method for forming the film; and a high-performing and highly reliable semiconductor device comprising the porous film inside. More specifically, provided is a composition for forming porous film, the composition comprising siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):



wherein X represents CO_2 , OSO_3 or SO_3 ; Y represents SO_4 , SO_3 , CO_3 , O_2C-CO_2 , NO_3 or NO_2 ; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1.